



Subject card

Subject name and code	Solid state electronics and nanoelectronics, PG_00071207						
Field of study	Nanotechnology, Nanotechnology						
Date of commencement of studies	February 2027	Academic year of realisation of subject			2026/2027		
Education level	second-cycle studies	Subject group			Specialty subject group Subject group related to scientific research in the field of study		
Mode of study	Full-time studies	Mode of delivery			at the university		
Year of study	1	Language of instruction			English		
Semester of study	1	ECTS credits			3.0		
Learning profile	general academic profile	Assessment form			exam		
Conducting unit	Division of Nanomaterials Physics -> Institute of Nanotechnology and Materials Engineering -> Faculty of Applied Physics and Mathematics -> Faculties of Gdańsk University of Technology						
Name and surname of lecturer (lecturers)	Subject supervisor	prof. dr hab. inż. Barbara Kościelska					
	Teachers	prof. dr hab. inż. Barbara Kościelska					
Lesson types	Lesson type	Lecture	Tutorial	Laboratory	Project	Seminar	SUM
	Number of study hours	30.0	0.0	0.0	0.0	0.0	30
	E-learning hours included: 0.0						
Learning activity and number of study hours	Learning activity	Participation in didactic classes included in study plan	Participation in consultation hours	Self-study	SUM		
	Number of study hours	30	2.0	43.0	75		
Subject objectives	The aim of the course is to acquire knowledge, skills and competence in the field of solid state electronics and nanoelectronics.						
Learning outcomes	Course outcome	Subject outcome			Method of verification		
	[K7_W02] has in-depth, theoretically grounded and detailed knowledge of phenomena, methods, and theories related to nanotechnology, as well as of related and allied fields of science or engineering	The student has in-depth knowledge of solid state electronics and nanoelectronics.			[SW1] Assessment of factual knowledge		
	[K7_W03] has knowledge of current development trends and the latest discoveries in the fields of physics, chemistry, technology, and applications of nanostructures	The student has knowledge of current developments in the field of solid-state electronics and nanoelectronics.			[SW1] Assessment of factual knowledge		
	[K7_U06] is able to apply acquired specialist knowledge to problems in other physical, natural, or technical sciences and to critically analyze and evaluate the functioning of the adopted solutions	The student is able to apply knowledge of physics and nanotechnology to issues related to solid state electronics and nanoelectronics.			[SU3] Assessment of ability to use knowledge gained from the subject		

Subject contents	<p>Course content – lecture</p> <ol style="list-style-type: none"> 1. Introduction. 2. Physics and properties of solids - a review <ol style="list-style-type: none"> 2.1. Density of states in 0D, 1D, 2D and 3D materials. 2.2. Band structure of solids: free electron, nearly free electron and tight binding model. 2.3. Energy bands and carrier concentration in thermal equilibrium. 2.4. Electrical and thermal conduction in solids: carrier transport phenomena. 2.5. Kinetic phenomena in semiconductors. 3. Metal-semiconductor junctions and p-n junctions. 4. Diodes: Schottky diode, p-n diode, MIS, MOS, tunnel diode, resonant-tunneling diode. 5. Transistors: bipolar, FET, hot-electron HET and THET, single-electron transistor. 6. Light emitting diodes and lasers. <ol style="list-style-type: none"> 6.1. Light emitting diodes. 6.2. Semiconductor lasers. 6.3. Quantum-cascade laser. 7. Photodetectors and solar cells. 8. Tunnel phenomena in superconductors: Josephson junction. 9. Spintronic devices. 10. Semiconductor technology. <ol style="list-style-type: none"> 10.1. Crystal growth and epitaxy. 10.2. Film formation. 10.3. Lithography and etching. 10.4. Impurity doping. 								
Prerequisites and co-requisites	Completed courses in the field of basics of nanotechnology and solid state physics (or physics of materials).								
Assessment methods and criteria	<table border="1"> <thead> <tr> <th data-bbox="453 1935 798 1966">Subject passing criteria</th> <th data-bbox="802 1935 1141 1966">Passing threshold</th> <th data-bbox="1145 1935 1485 1966">Percentage of the final grade</th> </tr> </thead> <tbody> <tr> <td data-bbox="453 1973 798 2004">written test</td> <td data-bbox="802 1973 1141 2004">50.0%</td> <td data-bbox="1145 1973 1485 2004">100.0%</td> </tr> </tbody> </table>	Subject passing criteria	Passing threshold	Percentage of the final grade	written test	50.0%	100.0%		
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Recommended reading	Basic literature	1. S.O. Kasap "Principles of electronic materials and devices", McGraw-Hill, 2006, 3rd ed. (EI 178223-00-00/01) 2. S.M. Sze, Kwok K. Ng, Physics of Semiconductor Devices, John Wiley & Sons, 2007, 3rd ed. (FM 304796-00-00/01)
	Supplementary literature	1. S.M. Sze, M.K. Lee Semiconductor Devices, Physics and Technology, John Wiley & Sons, 2012, 3rd ed.
	eResources addresses	
Example issues/ example questions/ tasks being completed	Describe metal-semiconductor junction Describe MOS diode Describe single electron transistor Describe quantum-cascade laser	
Practical activities within the subject	Not applicable	

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